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Sub
01

21. (TWICE AMENDED) A MEMS formation method including:
providing a SOI wafer including a single crystal silicon layer attached to an
insulator layer;
forming at least one first MEMS component by patterning the single crystal silicon
layer;
depositing at least one layer of polysilicon on the patterned single crystal silicon;
and
forming at least one second MEMS component by patterning the polysilicon.

Sub
02

23. (AMENDED) The method of claim 21 wherein the at least one second MEMS
component is a hinge.

Sub
03

30. (TWICE AMENDED) A MEMS device comprising:
at least one single crystal silicon component bonded to an insulator that rests on a
handle wafer; and
a polysilicon hinge derived from a layer of polysilicon applied over the at least one
single crystalline component.